

SANYO	No.2679A	2SC4291
		NPN Triple Diffused Planar Silicon Transistor Ultrahigh-Definition Color Display Horizontal Deflection Output Applications

Features

- High speed ($t_f = 0.3 \mu s$ max).
- High breakdown voltage ($V_{CBO} = 1500V$).
- High reliability (Adoption of HVP process).
- Adoption of MBIT process.
- On-chip damper diode.

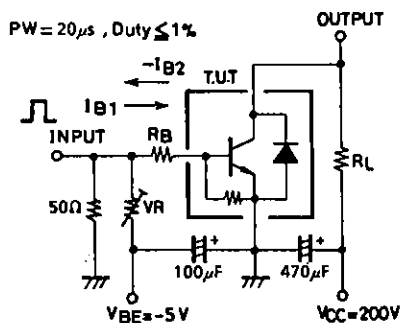
Absolute Maximum Ratings at $T_a = 25^\circ C$

			unit
Collector-to-Base Voltage	V_{CBO}	1500	V
Collector-to-Emitter Voltage	V_{CEO}	800	V
Emitter-to-Base Voltage	V_{EBO}	7	V
Collector Current	I_C	5	A
Collector Current (Pulse)	I_{CP}	16	A
Collector Dissipation	P_C	2.5	W
		$T_c = 25^\circ C$	
Junction Temperature	T_j	100	W
Storage Temperature	T_{stg}	150	$^\circ C$
		-55 to +150	$^\circ C$

Electrical Characteristics at $T_a = 25^\circ C$

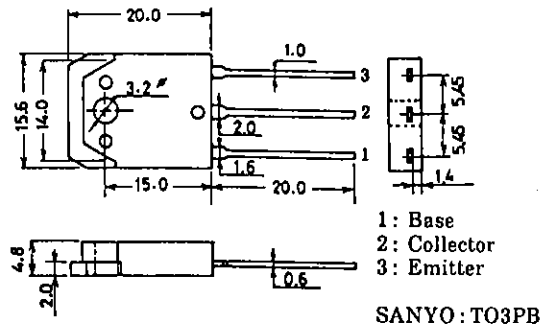
			min	typ	max	unit
Collector Cutoff Current	I_{CES}	$V_{CE} = 1500V$			1.0	mA
Collector Cutoff Current	I_{CBO}	$V_{CB} = 800V, I_E = 0$			10	μA
Collector Sustain Voltage	$V_{CEO(sus)}$	$I_C = 100mA, I_B = 0$	800			V
Emitter Cutoff Current	I_{EBO}	$V_{EB} = 4V, I_C = 0$	40		130	mA
C-E Saturation Voltage	$V_{CE(sat)}$	$I_C = 4A, I_B = 1A$			5	V
B-E Saturation Voltage	$V_{BE(sat)}$	$I_C = 4A, I_B = 1A$			1.5	V
DC Current Gain	$h_{FE(1)}$	$V_{CE} = 5V, I_C = 1A$	8			
	$h_{FE(2)}$	$V_{CE} = 5V, I_C = 4A$	4		6	
Diode Forward Voltage	V_F	$I_{EC} = 5A, I_B = 0$			2.0	V
Storage Time	t_{stg}	$I_C = 4A, I_{B1} = 0.8A, I_{B2} = -1.6A$			3.0	μs
Fall Time	t_f	$I_C = 4A, I_{B1} = 0.8A, I_{B2} = -1.6A$			0.3	μs

Switching Time Test Circuit



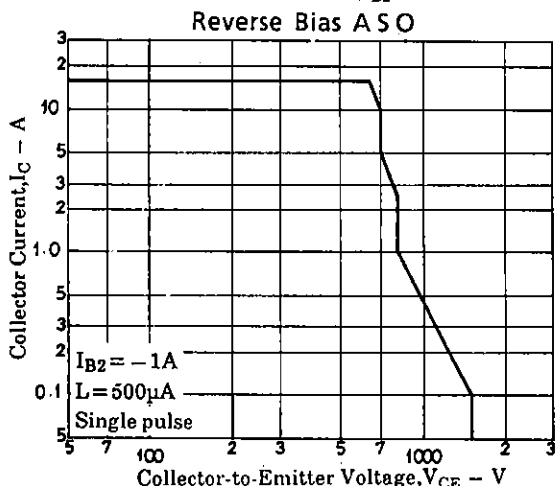
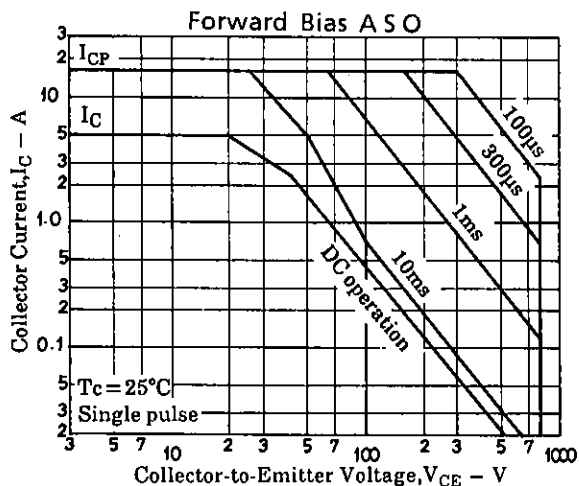
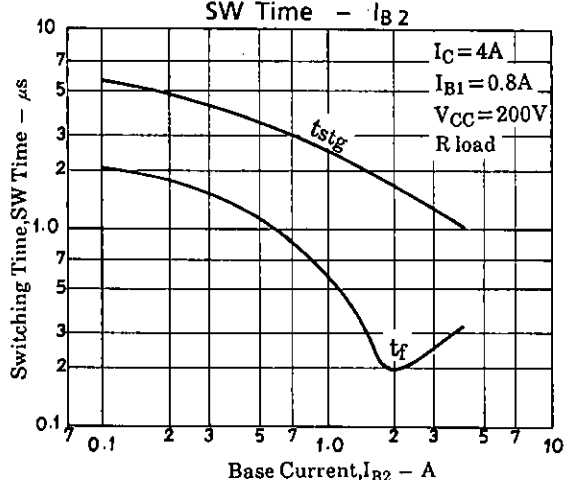
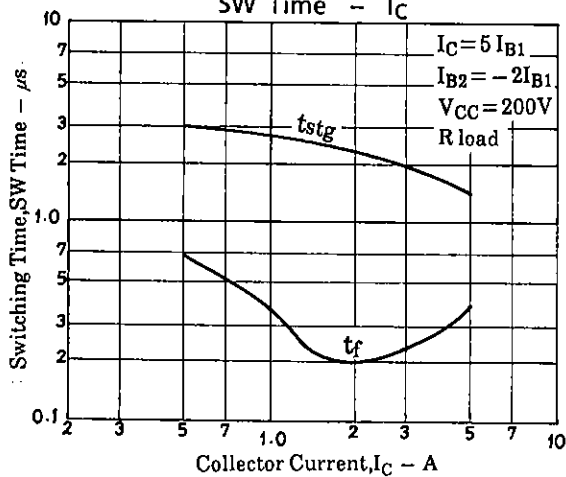
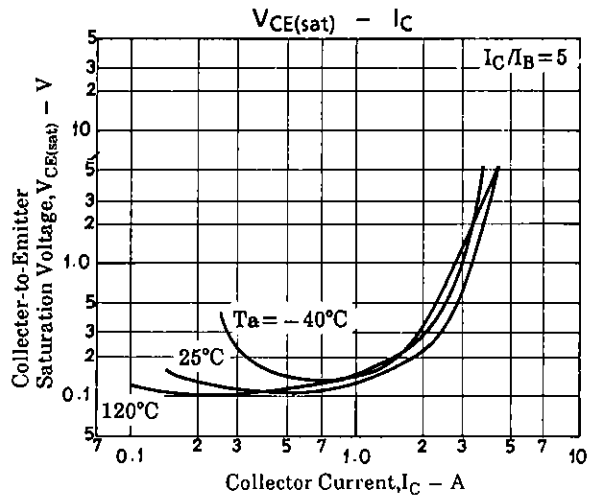
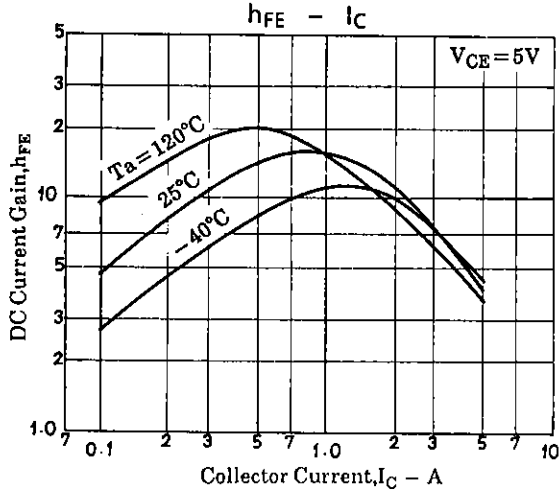
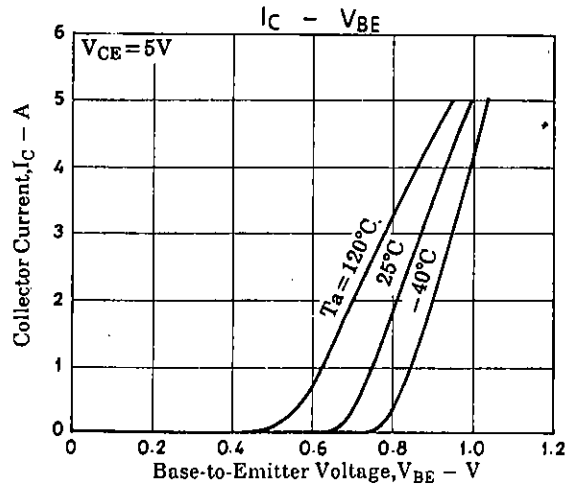
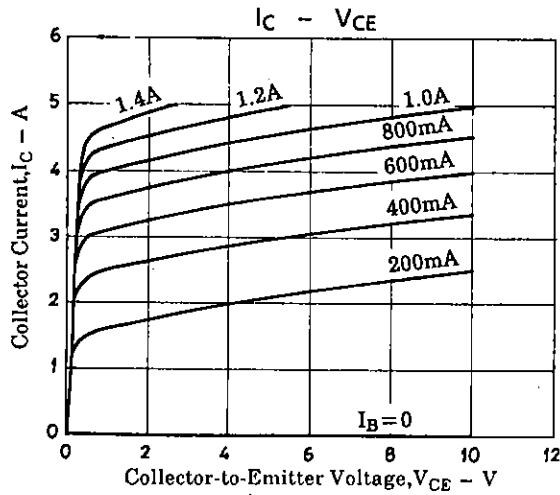
Package Dimensions 2022A

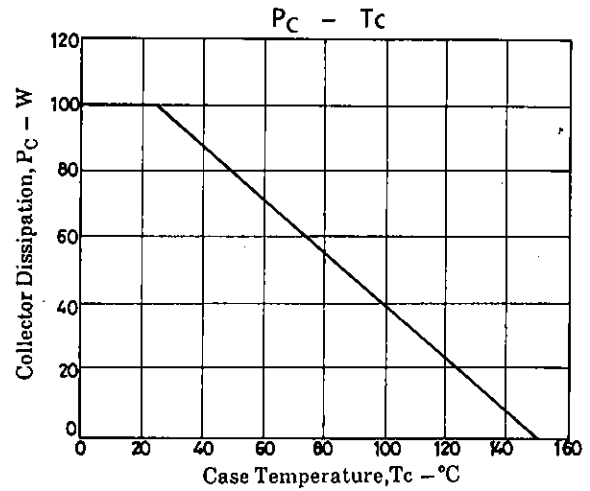
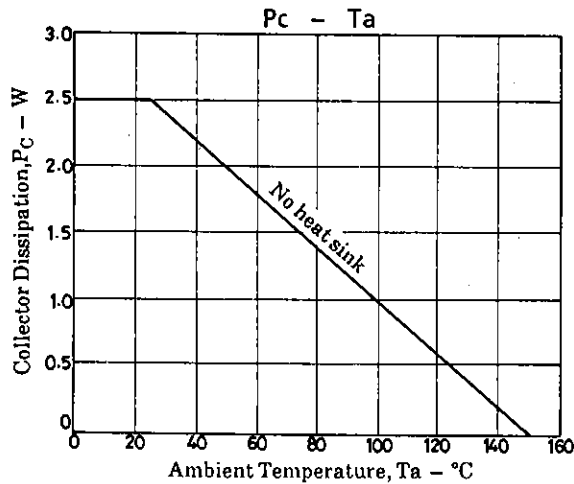
(unit : mm)



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